

	Hits	Search Text	DBs
30	11	((resist or photoresist) same (pattern or hole or via) same (exposure or (predetermined near5 amount) or illumination) and ((pattern or hole or via or (line near6 space)) same (aspect near5 ratio) same LSI) and ((resist near4 pattern) same (thicken\$4 or improv\$4 or enhanc\$4 or coat\$4 or top\$4coat\$4) same (heat\$4 or bak\$4) same (thickness or nm or micron))	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB
31	5	((resist or photoresist) same (pattern or hole or via or opening) same (exposure or (irradiat\$4) or illumination) same (dimension or size)) and ((pattern or hole or via or (line near6 space)) same (aspect near5 ratio) same LSI) and ((resist near4 pattern) same (thicken\$4 or improv\$4 or enhanc\$4 or coat\$4 or top\$4coat\$4) same (heat\$4 or bak\$4))	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB
32	0	((resist or photoresist) same (pattern or hole or via or opening) same (exposure or (irradiat\$4) or illumination) same (dimension or size)) and ((pattern or hole or via or (line near6 space)) same (aspect near5 ratio) same LSI) and ((resist near4 pattern) same (thicken\$4 or improv\$4 or enhanc\$4 or coat\$4 or top\$4coat\$4) same (heat\$4 or bak\$4))	USOCR

	Hits	Search Text	DBs
33	5	((resist or photoresist) same (pattern or hole or via or opening) same (exposure or (irradiat\$4) or illumination) same (dimension or size)) and ((pattern or hole or via or (line near6 space)) same (aspect near5 ratio) same LSI) and ((resist near4 pattern) same (thicken\$4 or improv\$4 or enhanc\$4 or coat\$4 or top\$4coat\$4 or smoothen\$5) same (heat\$4 or bak\$4))	US-PGPUB; USPAT